

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	26	crystal defect same etch\$3 same evaluat\$4 and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:42
L3	252	crystal defect and (secco or sertl or wright) with etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:43
L4	42	crystal defect same (secco or sertl or wright) with etch\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:45
L5	4	crystal defect same (secco or sertl or wright) with etch\$4 and second near solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:52
L6	4	crystal defect and (secco or sertl or wright) with etch\$4 and second near solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:53
L7	4	crystal defect and (secco or sertl or wright) same etch\$4 and second near solution	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:53
L8	1	crystal defect and evalut\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:54
L9	0	crystal defect and evalutuat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:54

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L10	2209	crystal defect and evaluat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:54
L11	16	crystal defect same evaluat\$3 same reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:07
L12	0	crystal defect same evaluat\$3 same reference wafer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:07
L13	1	crystal defect same evaluat\$3 same reference area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:08
L14	1	crystal defect and evaluat\$3 same reference area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:08
L15	4	crystal defect and evaluat\$3 and reference area	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 08:12
L16	448	(438/5).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/24 08:12
L17	418	(438/7).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/24 08:12

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L18	253	(438/8).CCLS.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/24 09:02
L19	0	("crystaldefectandhfwithconcentration").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/07/24 09:03
L20	154	crystal defect and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:03
L21	39	crystal defect and evaluat\$3 and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:03
L22	1	crystal defect and evaluat\$3 and hf with concentration and defect free	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:04
L23	1	crystal defect and evaluat\$3 and hf with concentration and defect-free	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:04
L24	39	crystal defect and evaluat\$3 and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:28
L25	1	crystal defect and evaluat\$3 and defect free reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:06

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L26	10	crystal defect and evaluat\$3 and defect free with reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:20
L27	0	crystal defect and evaluat\$3 and defect free with reference image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
L28	1	crystal defect and evaluat\$3 and defect free and reference image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
L29	1	crystal defect and defect free and reference image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
L30	185	defect free and reference image	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
L31	8	defect free and reference image and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:08
L32	2	crystal defect and evaluat\$3 and defect free with reference and no defect	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:20
L33	11	crystal defect and evaluat\$3 and ((defect free) or (no defect)) with reference	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:21

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L34	47	crystal defect and (evaluat\$3 or detection) and hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:28
L35	1	crystal defect and (evaluat\$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:30
L36	1	crystal defect and (evaluat\$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 09:30
L37	36	defect and (evaluat\$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:00
L38	0	defect and (evaluat\$3 or detection) same hydrofluoric with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:01
L39	220	defect and (evaluat\$3 or detection) and hydrofluoric with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:01
L40	12	defect and (evaluat\$3 or detection) same hydrofluoric with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:08
L41	58	crystal defect and (evaluat\$3 or detection) same hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:09

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L42	1	crystal defect and (evaluat\$3 or detection) same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:10
L43	10	crystal defect same hf with concentration	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 10:10
S1	38	first solution with (hf or "nh.sub.4f") and second solution with (alkali or HF or acid)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:31
S2	21	first solution with (hf or "nh.sub.4f") and second solution with (alkali or HF or acid) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 19:45
S3	32	first near solution with (hf or "nh.sub.4f") and second near solution with (alkali or HF or acid) and semiconductor	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 19:45
S4	1	deffect same etch\$3 and evaluat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:40
S5	3124	defect same etch\$3 and evaluat\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:40
S6	551	defect same etch\$3 and evaluat\$4 and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:40

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S7	13	defect same etch\$3 and evaluat\$4 and hf and "Nh.sub.4f"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:44
S8	4	defect same etch\$3 same evaluat\$4 and hf and "Nh.sub.4f"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/21 20:46
S9	103	defect same etch\$3 same evaluat\$4 and hf	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	ADJ	ON	2006/07/24 07:24